PAN	JIT
	SEMI
	CONDUCTOR

#### 60V Dual N-Channel Enhancement Mode MOSFET

Current

Voltage

### Features

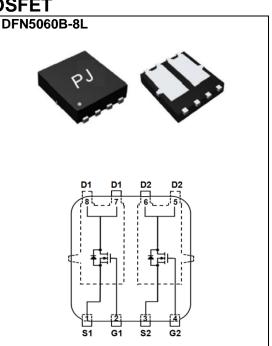
• R<sub>DS(ON)</sub>, V<sub>GS</sub>@10V, I<sub>D</sub>@20A<17mΩ

60 V

- R<sub>DS(ON)</sub>, V<sub>GS</sub>@4.5V, I<sub>D</sub>@10A<20mΩ
- High switching speed
- Improved dv/dt capability
- Low reverse transfer capacitance
- AEC-Q101 qualified
- Lead free in compliance with EU RoHS 2.0
- Green molding compound as per IEC 61249 standard

#### **Mechanical Data**

- Case : DFN5060B-8L Package
- Terminals : Solderable per MIL-STD-750, Method 2026
- Approx. Weight : 0.0035 ounces, 0.092 grams



#### **Maximum Ratings and Thermal Characteristics** (T<sub>A</sub>=25°C unless otherwise noted)

40 A

PARAMETE	R	SYMBOL	LIMIT	UNITS	
Drain-Source Voltage		V <sub>DS</sub>	60	N/	
Gate-Source Voltage		V <sub>GS</sub>	<u>+</u> 20	V	
Continuous Droin Current (Note 4)	Tc=25°C		40		
Continuous Drain Current (Note 4)	T <sub>C</sub> =100°C		25	А	
Pulsed Drain Current (Note 1)	Tc=25°C	I <sub>DM</sub>	160		
Power Dissipation	Tc=25°C	Po	68.2	W	
	Tc=100°C		34.1		
Quarting on During Quarter of (Note 4)		7			
Continuous Drain Current (Note 4)	T <sub>A</sub> =70°C	Ι <sub>D</sub>	5.5	A	
	T <sub>A</sub> =25°C	PD	2.0	14/	
Power Dissipation	T <sub>A</sub> =70°C		1.4	W	
Single Pulse Avalanche Energy (Note 6)		E <sub>AS</sub>	45	mJ	
Operating Junction and Storage Temperature Range		T <sub>J</sub> ,T <sub>STG</sub>	-55~175	°C	
Typical Thermal Resistance (Note 4,5)	Junction to Case	R <sub>eJC</sub>	2.2	∘C/W	
	Junction to Ambient	R <sub>θJA</sub>	73.5		

• Limited only By Maximum Junction Temperature



#### Electrical Characteristics (T<sub>A</sub>=25°C unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS
Static			-			-
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V, I <sub>D</sub> =250uA	60	-	-	v
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250uA	1	1.7	2.5	
Drain-Source On-State Resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> =10V, I <sub>D</sub> =20A	-	13	17	mΩ
Drain-Source On-State Resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> =4.5V, I <sub>D</sub> =10A	-	16	20	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =60V, V <sub>GS</sub> =0V	-	-	1	uA
Gate-Source Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> = <u>+</u> 20V, V <sub>DS</sub> =0V	-	-	<u>+</u> 100	nA
Dynamic (Note 7)						
Total Gate Charge	Qg	V <sub>DS</sub> =30V, I <sub>D</sub> =10A,	-	13.5	-	
Gate-Source Charge	Qgs		-	4.8	-	nC
Gate-Drain Charge	Qgd	V <sub>GS</sub> =4.5V (Note 2,3)	-	4.9	-	
Input Capacitance	Ciss		-	1574	-	
Output Capacitance	Coss	$V_{DS}=25V, V_{GS}=0V,$	-	118	-	pF
Reverse Transfer Capacitance	Crss	f=1MHZ	-	77	-	
Turn-On Delay Time	td(on)		-	11	-	
Turn-On Rise Time	tr	$V_{DD}=15V, I_D=1A,$	-	11	-	
Turn-Off Delay Time	td(off)	V <sub>GS</sub> =10V, R <sub>G</sub> =6Ω	-	35	-	ns
Turn-Off Fall Time	tf		-	8.1	-	
Drain-Source Diode						
Maximum Continuous Drain-Source					10	
Diode Forward Current	I <sub>S</sub>		-	-	40	A
Diode Forward Voltage	V <sub>SD</sub>	Is=1A, V <sub>GS</sub> =0V	-	0.68	1	V

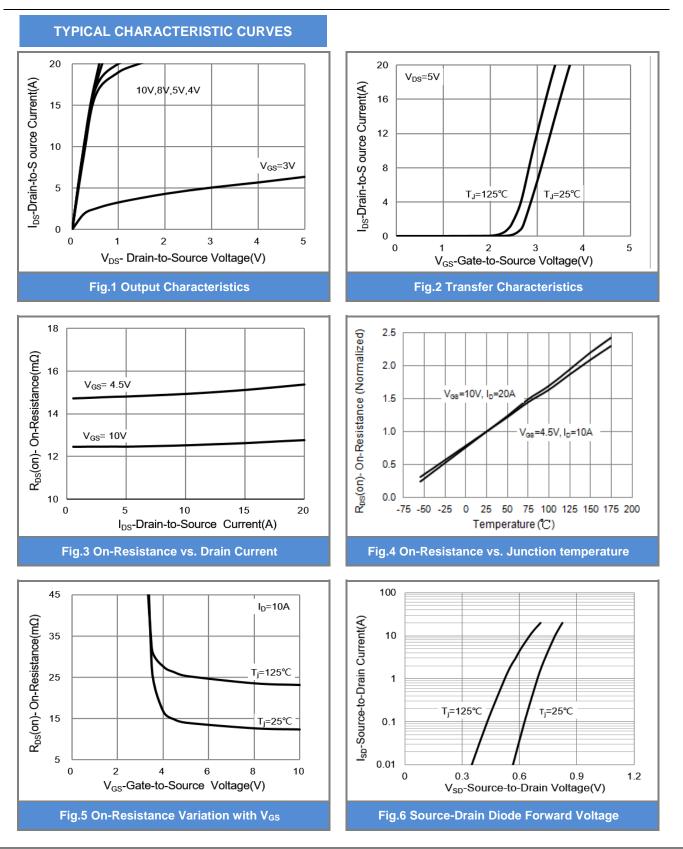
NOTES :

- 1. Pulse width</br>
- 2. Essentially independent of operating temperature typical characteristics.
- Repetitive rating, pulse width limited by junction temperature T<sub>J(MAX)</sub>=150°C. Ratings are based on low frequency and duty cycles to keep initial T<sub>J</sub> =25°C.
- 4. The maximum current rating is package limited.
- 5. R<sub>®JA</sub> is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. Mounted on a 1 inch<sup>2</sup> with 2oz.square pad of copper.
- 6. The test condition is L=0.1mH,  $I_{AS}$ =30A,  $V_{DD}$ =25V,  $V_{GS}$ =10V, Starting  $T_J$ =25°C.
- 7. Guaranteed by design, not subject to production testing.

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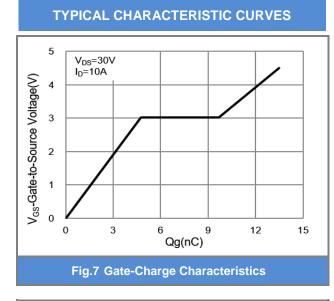
### PJQ5866A-AU



SEMI CONDUCTOR

PΛN

## PJQ5866A-AU



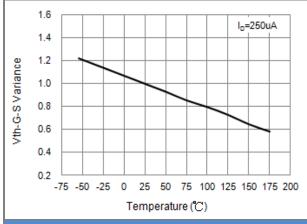
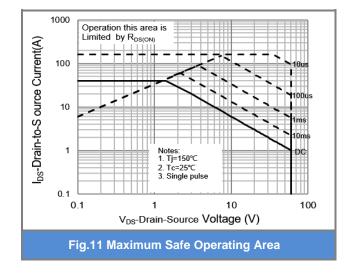
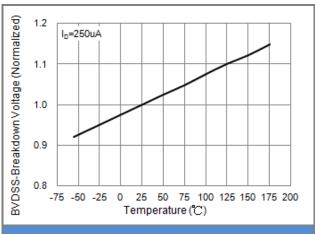


Fig.9 Threshold Voltage Variation with Temperature







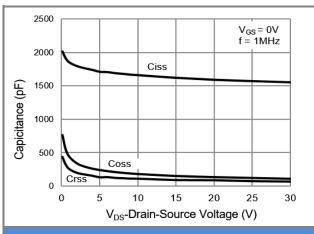
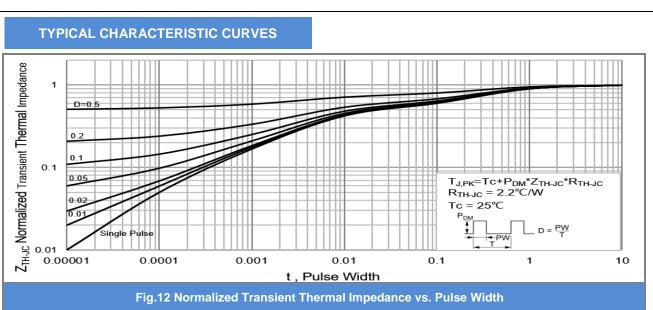


Fig.10 Capacitance vs. Drain-Source Voltage



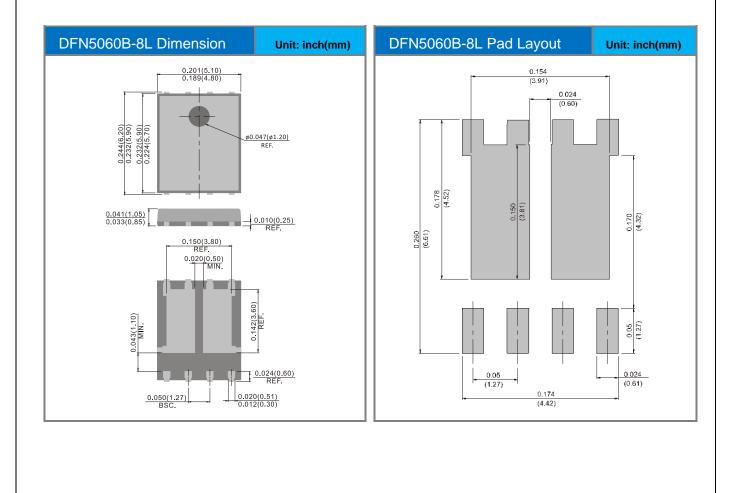




#### **Product and Packing Information**

Part No.	Package Type	Packing Type	Marking
PJQ5866A-AU	DFN5060B-8L	3000pcs / 13" reel	Q5866A

#### Packaging Information & Mounting Pad Layout





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